

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A power semiconductor module comprising
- at least one semiconductor chip ~~(11)~~ made of a semiconductor material and having a first and a second main electrode,
 - a first and second main connection ~~(91, 92)~~,
 - a contact lamina ~~(2)~~ in electrical contact with the first main electrode and the first main connection ~~(92)~~,
 - the contact lamina ~~(2)~~ containing an alloying partner and it being possible for a eutectic to be formed between the alloying partner and the semiconductor material,
 - the contact lamina being coated with an electrically conductive protective layer ~~(31, 32)~~,

wherein characterized in that

- the protective layer ~~(31, 32)~~ has at least one electrically conductive base layer ~~(31)~~ applied on the contact lamina ~~(2)~~, and
- an electrically conductive surface layer ~~(32)~~, which forms the external contact area,

and in that

- the base layer and the surface layer substantially comprise different materials.

2. (Currently Amended) The power semiconductor module as claimed in claim 1, wherein ~~characterized in that~~

- the base layer (31) substantially comprises Ni and preferably has a thickness of between approximately 1 μm and 15 μm , preferably between 2 μm and 8 μm .

3. (Currently Amended) The power semiconductor module as claimed in claim 1 ~~or 2~~, wherein ~~characterized in that~~

- the surface layer (32) has a thickness of between approximately 0.1 μm and 5 μm .

4. (Currently Amended) The power semiconductor module as claimed in claim one of claims 1 to 3, wherein ~~characterized in that~~

- the surface layer (32) substantially comprises Ru,
- an electrically conductive intermediate layer is provided between the surface layer (32) and the base layer (31), said intermediate layer substantially comprising Au and preferably having a thickness of approximately 0.2 μm , and
- the base layer (31) preferably has a thickness of between 5 μm and 12 μm .

5. (Currently Amended) The power semiconductor module as claimed in claim 1 one of the preceding claims, wherein ~~characterized in that~~

- the semiconductor chip (11) internally has an IGBT structure or a diode structure.

6. (Currently Amended) The power semiconductor module as claimed in claim 1,
wherein characterized in that

- the base layer ~~(31)~~ comprises a good covering material, and in that
- the surface layer ~~(32)~~ comprises a material having one or more of the following properties:
 - a non-oxidizable, preferably exhibiting little chemical reactivity,
 - b does not react chemically with a first electrode metallization of the first main electrode and exhibits neither contact corrosion nor material diffusion,
 - c has a low coefficient of friction,
 - d can be deposited at temperatures at which the contact layer is not damaged or deformed.